TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SA1987

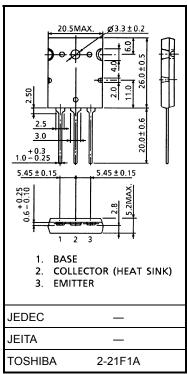
Power Amplifier Applications

Unit: mm

- High breakdown voltage: $V_{CEO} = -230 \text{ V (min)}$
- Complementary to 2SC5359
- Recommended for 100-W high-fidelity audio frequency amplifier output stage.

Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-230	V
Collector-emitter voltage	V _{CEO}	-230	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	IC	-15	Α
Base current	Ι _Β	-1.5	Α
Collector power dissipation (Tc = 25°C)	P _C	180	W
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	−55 to 150	°C



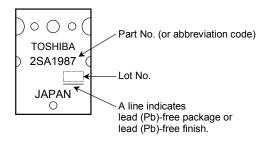
Weight: 9.75 g (typ.)

Electrical Characteristics (Tc = 25°C)

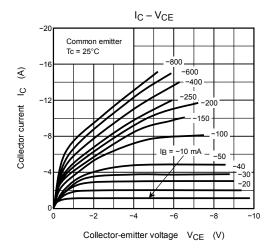
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = -230 V, I _E = 0	_	_	-5.0	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V, I _C = 0	_	_	-5.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -50 \text{ mA}, I_B = 0$	-230	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = -5 V, I _C = -1 A	55	_	160	
	h _{FE (2)}	V _{CE} = -5 V, I _C = -7 A	35	70	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = -8 A, I _B = -0.8 A	_	-1.5	-3.0	V
Base-emitter voltage	V_{BE}	V _{CE} = -5 V, I _C = -7 A	_	-1.0	-1.5	V
Transition frequency	f _T	V _{CE} = -5 V, I _C = -1 A	_	30	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	360	_	pF

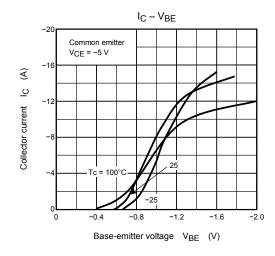
Note: $h_{FE\ (1)}$ classification R: 55 to 110, O: 80 to 160

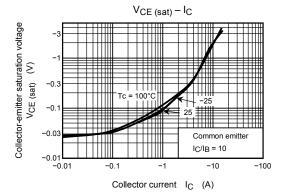
Marking

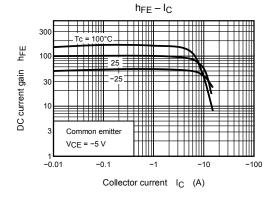


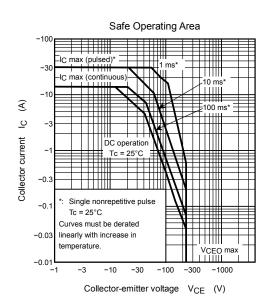
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3 2004-07-07

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